

Remarks:

This amendment is submitted in an earnest effort to advance this case to issue without delay.

The specification has been amended to eliminate some minor obvious errors. No new matter whatsoever has been added.

Enclosed herewith is a PTO-1449 listing the US equivalent of German 101 18 130 cited in the earlier-filed PTO-1449, giving the correct number for the EP Shibata reference (1,207,215, not 1,027,215), and listing the US equivalent (2002/0094682) of the EP '215 Shibata reference.

The claims have been amended to define the invention more clearly over the art.

EP '215 and US '682 of Shibata do not show a MOCVD apparatus with means for flexibly controlling gas at the inlets. The examiner's analysis of this reference in paragraph 8 of the Action is incorrect. In Shibata to change the gas feed it is necessary to completely disconnect the supplies for the gases, which is a time-consuming chore. The inlets 15, 16, and 17 are permanent parts of the apparatus with no way to switch around the gases.

US 6,218,212 of Saito is largely cumulative to Shibata in that it also does not show flexible gas control. The valves 37 shown in FIG. 4B do not control gas flow into the apparatus, but (see column 5, lines 28-34) for mass flow control.

Cited but not applied US 6,960,537 of Shero describes in column 7, lines 35 that supplies 63 and 64 are connected via a gas line 62 to a species generator 60. The valves merely determine which gas goes to the generator 60. This relates once again only to mas control and not to a flexible switching of the valves in different compartments of the apparatus.

The closest art is indeed Saito that shows an MOCVD apparatus with various valves (see FIG. 3). Saito does not show a system for reversing connections between the sources and the two compartments. This system makes it possible to feed either of the compartments 4' or 5' (FIG. 5) with either gas.

The object of the invention is to be able to determine which gas is fed to which compartment without having to disconnect and reconnect the various supplies. Thus in case on deposition of for example Group III nitrides, parasitic depositions on the inner surfaces of the deposition chamber are avoided.

Saito teaches nothing like this since there the valves serve purely for mass-flow control. The bubbler 1 can only feed gas tot he inlet port 11, and the bubbler 3 can only supply gas to the inlet port 13 and thence into the compartment 15. The valves

37 shown in FIG. 4B for mass-flow control, that is whether gas flows from the bubblers 1, 2, and 3 into the respective inlet ports 11, 12 13 and thence into the apparatus or not. There is no means for feeding the gas from the bubbler 1 into the port 13, that is there is no disclosure for selective feed of any gas to any compartment, because the problem of parasitic deposition is apparently not recognized. Thus there is no suggestion for the system as defined in claim 15.

Based on the teachings of Saito the person skilled in the art would, with the teachings of Shero, not come to the idea of switching the gas flows between the compartments. This is because Shero does not even show different compartments; instead the gases are fed. via a species generator 60 into the apparatus. The valves again serve for mass-flow control, not for switchover.

The invention is based on the discovery that for some depositions in semiconductor technology it is important to be able to feed a given gas sometimes into the upper compartment, sometimes in to the lower compartment to prevent parasitic depositions. In order to avoid having to deinstall and reconnect a supply, the system of claim 15 is employed.

Shibata does not to a MOCVD system where gases can be flexibly and selectively fed to the various compartments. In fact the Shibata system does nothing significant to prevent depositions on the chamber walls, which depositions can drop off the hot walls onto the wafer, creating a defective product.

Nothing in the art suggests a system for selectively and flexibly feeding the treatment gases in an MOCVD apparatus to the different compartments of the deposition chamber. The valves of Saito and Shero serve only for mass-flow control, not for complete flow switchover.

Thus the claims in the case clearly define patentable invention over the prior art. Allowance of all claims is in order.

If only minor problems that could be corrected by means of a telephone conference stand in the way of allowance of this case, the examiner is invited to call the undersigned to make the necessary corrections.

K.F. Ross P.C.

/Andrew Wilford/

by: Andrew Wilford, 26,597
Attorney for Applicant

11 September 2008
5683 Riverdale Avenue Box 900
Bronx, NY 10471-0900
Cust. No.: 535
Tel: 718 884-6600
Fax: 718 601-1099
Email: email@kfrpc.com

Enclosure: Marked Specification
 Clean Specification
 Replacement drawing (5 sheets)
 PTO-1449

~~METHOD OF DEPOSITING COMPOUNDS ON A SUBSTRATE BY MEANS OF METAL ORGANIC MOCVD GAS-PHASE DEPOSITION APPARATUS~~

CROSS REFERENCE TO RELATED APPLICATIONS

This application is the US national phase of PCT

5 application PCT/DE2004/000315, filed 20 February 2004, published 07 October 2004 as WO 2004/085702, and claiming the priority of German patent application 10312768.2 itself filed 21 March 2003 and German patent application 10325629.6 itself filed 6 June 2003, whose entire disclosures are herewith incorporated by reference.

10 FIELD OF THE INVENTION

The invention relates to an apparatus for method of depositing compounds on a substrate by means of metal organic gas-phase deposition.

BACKGROUND OF THE INVENTION

15 Metal-organic gas-phase deposition (metal-organic chemical vapor deposition: [[()]] MOCVD) is a method of making layer structures of a complex configuration as can be used in electronic components, for example, high-speed transistors for Handys cell phones or light-emitting diodes. By contrast to known silicon structures, these structures are composed not of one element but from two or even more elements. They can be referred to therefore also as compound semiconductors. The metal organic gas-phase deposition is carried out in a so-called MOCVD apparatus.

20

With the MOCVD apparatus, nitride layers among others can be deposited and can be comprised of two elements, like for

5

example, GaN, InN or AlN or from more elements like for example GaInN or AlGaN. These compounds are referred to as binary or ternary systems for the monocrystalline deposition of nitride compounds, sapphire (Al_2O_3) or silicon carbide (SiC) or silicon, which have similar crystal characteristics to the nitrides are used as substrates.

The group III nitrides include through their representatives a semiconductor system with direct band gaps of 1.9 eV for InN to 6.2 eV for the aluminum nitride AlN.

10

These nitride layers are economically very significant since they can emit light in the blue part of the visible spectrum upon electrical excitation and thus can be used to make optoelectronic components which are useful in the corresponding energy range. As an example of this are pn light-emitting diodes on the basis of GaN.

15

For metal organic gas-phase deposition of nitride layers one requires gas-phase compounds of gallium, indium or aluminum as well as NH_3 as so-called precursors. In the case of gallium, a metal organic compound, for example trimethylgallium (TMG) is used. By means of a carrier gas, for example hydrogen, the precursor is carried into a reaction compartment of the apparatus. There is found the substrate, a monocrystalline very thin disk (wafer) which can be heated. The wafer is mounted so as to rotate on a so-called susceptor to produce a uniform distribution of temperature and precursor in the gas phase over the substrate. With an infrared radiator or high-frequency heating the susceptor and the substrate

20

25

are heated. The temperature of the substrate reaches about 1500°C depending upon which material systems is deposited. This region is also designated as the hot zone.

For the deposition upon the substrate, the precursor is transformed. This occurs in part already in the gas phase as a result of the heat which is emitted by the substrate or by impingement of molecules of the carrier gas thereon. The molecular fragments deposit upon the substrate surface. As a result of the high temperature the original precursor compounds decompose and react to form new compounds, for example, GaN, InN or AlN. In this manner a new layer grows upon the wafer in atomic layer after atomic layer as GaN, InN or AlN. The residues of the starting molecules, for example methyl groups from TMG and hydrogen combine partly with one another to form methane. Molecules which do not deposit or adhere and molecular fragments are released from the surface and like the methane are carried off with the carrier gas stream and are discharged from the MOCVD apparatus to a gas cleaning system, a so-called scrubber, for removal.

An MOCVD apparatus usually has two gas inlets and provisions for dividing the gas streams which are to be introduced into the apparatus so that an instantaneous mixing within the apparatus, which could lead to the formation of acid-based adducts prematurely, can be avoided. For this purpose a partition or separator plate can be so arranged downstream of the gas inlets of the apparatus that the MOCVD apparatus is compartmented into an upper and a lower space. Outside the apparatus, gas supply lines

or manifolds are provided which can be connected to supply vessels. In these supply vessels the starting materials are held in readiness, for example on the one hand the metal organics and on the other hand group V or group VI compounds.

5 A drawback is that up to now it has not been possible to flexibly distribute the gases within the compartments of the apparatus.

In the formation by the aforedescribed technology of, for example, group III nitride layers by means of gas phase deposition 10 in an MOCVD apparatus, precursors together with their carrier gases (H_2 , N_2 , argon) are each separately fed into the apparatus. The gas streams are first mixed in the hot zone of the apparatus in order to ensure a stable nitride surface at which at the growth temperature nitrogen may be volatile, the carrier gas/ NH_3 mixture (Group V compounds) according to the state of the art is locally 15 introduced more closely to the growth surface at the substrate than the carrier gas/metal-organic mixture. As a consequence the hot surface of the substrate will cause nitrogen to be liberated from the ammonia and to be available for reaction upon the substrate. This approach has also been used for the deposition of other 20 compounds as well.

A drawback of this system is that the nitrides which are formed also tend to deposit rapidly parasitically on the hot walls 25 of the apparatus. The nature and thicknesses of these deposits vary in the course of the method. The parasitic deposits cause variations in the growth on the substrate by catalytic

5

decomposition of the starting compound and the reduction in concentration in the gas phase as a result. Since the deposited compounds are of a dark coloration, they influence the gas phase temperature and the surface temperature of the substrate. The nitride layers can thus not be reproducibly formed on the substrate.

10

The parasitic deposits flake off from the walls after a short time and the particles can then fall from the parasitic-deposit-coated parts of the apparatus upon the substrate or the sample and can have a detrimental effect on the characteristics of the layer or layers to be applied there.

15

As a solution to this problem, the parts of the apparatus, which have been coated by the parasitic deposition and which may come into contact with the substrate, are replaced or cleaned as soon as the parasitic deposit has accumulated to a critical level.

This however is detrimentally expensive since in the interim the apparatus cannot be used.

OBJECT OF THE INVENTION

20

The object of the invention is to provide an apparatus process for depositing a compound on a substrate by means of methyl metal organic gas-phase deposition without such parasitic deposits occurring. The object is achieved with a method with the feature of patent claim 1 and with an MOCVD apparatus with the features of patent claim 15. Advantageous features are also given in the patent claims respectively dependent thereon.

25

SUMMARY OF THE INVENTION

According to the invention, in the method a first mixture of at least carrier gas and at least one metal organic compound and a second mixture of at least one carrier gas and at least one Group V compound or Group VI compound are used, whereby both mixtures are separately admitted into an apparatus for depositing the compound upon the substrate. The method is characterized in that at least one metal organic compound is introduced between the substrate and the Group V or Group VI compound. The at least one metal organic compound is thus fed into the apparatus at a location which is closer to the substrate than the Group V or Group VI compound.

Advantageously this has the effect that the thickness of the parasitic deposition is significantly reduced since the deposit is formed practically exclusively where it is desired, namely upon the substrate. The deposition rate as a rule is increased and the coatings or layers are of higher purity by comparison with layers of coating which are deposited by state of art techniques.

The particle formations on the wall and the ceiling of the apparatus are reduced to a minimum. Many layers can be deposited reproducibly before parts coated by parasitic deposition of the apparatus must be replaced in an expensive operation and without the danger that materials separating from parasitic deposits will flake off and contaminate the deposited layer.

The metal organic compound can be selected from a Group II compound or a Group III compound or a Group IV compound. Only examples, barium/strontium compounds (Group II) or

5

trimethylgallium, trimethylaluminum and trimethylindium (Group III) or titanium isopropoxide (Group IV) are specifically mentioned only by way of example. As Group V compounds NH₃ and/or AsH₃ and/or PH₃ can be used and as Group VI compounds, oxygen or diethyldiethoxytelluride can be used.

10

It will be self-understood that the method is not limited to a selection from such compounds. Rather the method can basically be used for the deposition of compounds on a substrate by means of metal organic gas-phase deposition generally. As a carrier gas for the compounds, hydrogen and/or nitrogen and/or argon are to be considered.

For the deposition of for example GaN, trimethylgallium is selected as a Group III compound and NH₃ as the Group V compound with hydrogen as the respective carrier gas in each case.

15

In this case, the metal organic/carrier gas mixture is introduced between the substrate and the point at which the NH₃/carrier gas mixture is introduced. It is however possible without limiting the invention to carry out the process according to the invention with other compounds to avoid parasitic deposition.

20

An MOCVD apparatus has at least two gas inlets, a first for a first mixture and at least one second for a further mixture. The gases themselves derive from the supply vessels. Between the gas inlets of the apparatus and the supply vessels for the gases there are, according to the invention, means, especially at least 25 two three-way valves, arranged in so-called gas-collecting lines.

There can however also be suitable quick-connect couplings in these lines.

This enables advantageously the apparatus to be connected to the supply vessels and the gases to be flexibly introduced into the various compartments of the MOCVD apparatus in a flexible manner without each time requiring the apparatus to be separated from the supply vessels to be newly connected thereto.

In other words the operator of such an apparatus is able to supply gases based upon his requirements conveniently and flexibly into the parts of the apparatus at which they are required. For this purpose inlets for the gas mixtures can rapidly be exchanged for one another.

It is also conceivable for this purpose to provide other structural modifications to the apparatus.

15 BRIEF DESCRIPTION OF THE DRAWING

Below the invention will be described in greater detail based upon several embodiments or examples and the accompanying [[5]] five Figures in which:

FIG. 1 is a schematic perspective view of an MOCVD apparatus according to the invention;

FIG. 2 is a section through the apparatus of FIG. 1;

FIG. 3 illustrates mixing of gases in the apparatus;

http://www.allsitesaccess.com/more_cumfiesta.htm?id=ndmariod

FIGS. 4a and 4b are graphs illustrating the prior art and the present invention, respectively; and

FIG. 5 is a schematic illustration of the invention.

SPECIFIC DESCRIPTION

FIG. 1 shows schematically an MOCVD apparatus according to the state of the art with two gas inlets 4, 5 for an upper compartment and a lower compartment. Precursors are separated from one another by a partition plate 1 and are supplied to a substrate 2 to be coated. The MOCVD apparatus is compartmented by the partition 1 into an upper chamber and a lower chamber downstream of the gas inlets 4, 5. The substrate 2 can for example be a two unit wafer. Self-understood, moreover, is that the method is not limited to particular sizes or shapes of the substrate. The substrate 2 is mounted in a susceptor 6 which is here formed as a rotatable plate. The walls of the apparatus have only been indicated in the drawing. That is, only one wall has been illustrated substantively, namely the wall 3 in the present case. The front walls in the direction of view of the roof have not been illustrated to allow a look into the interior of the apparatus.

FIG. 2 is a cross section through the apparatus along an imaginary line between the inlets and a cooling unit 7 located upstream of the susceptor (not shown). The cooling unit 7 has been shown only representatively schematically in FIG. 2. In the present case, the gas inlet 5 is provided to introduce the metal organic/carrier gas mixture (TMG/H₂) and the gas inlet 4 for the NH₃/carrier gas mixture (NH₃/H₂). After the gases are admitted into the apparatus the two gas streams remain separated from one another initially by the partition 1 until they mix downstream of the partition plate 1 and contact the substrate on the susceptor. The

metal organic/carrier gas mixture is introduced between the substrate and the NH₃/carrier gas mixture.

FIG. 3 shows the mixing of the reactants above the cooling unit 7 shown only schematically and ~~shortly ahead~~ closely upstream of the susceptor 6. The more dense ammonia/carrier gas mixture diffuses in the direction of the substrate on the susceptor 6 where it mixes with the metal organic/carrier gas mixture. On and upstream of the substrate such that the decomposition of the precursor is catalytically accelerated, there is a precipitation of GaN. The total gas mixture does not reach the roof of the apparatus so that there too a parasitic deposition of GaN is avoided.

FIG. 4a shows the course of the deposition of GaN as will arise in the state of the art. The X axis shows the local coordinate along a substrate or a wafer. The wafer is represented by the [[black]] bar. The deposition rate after an hour amounts to only about 1.3 micrometer GaN.

The process according to the invention, in which the TMG/H₂ mixture is introduced according to the invention between the substrate and the NH₃ carrier gas mixture and thus locally more proximal to the substrate, enables on average a much higher deposition rate of about 4 to 5 micrometers GaN. Because of the rotatable susceptor 6, the deposit can be uniformly distributed across the wafer (FIG 4b). The higher deposition rate ahead of the wafer enables the deposition of GaN with much higher purity on this wafer.

The higher deposition rate in this latter case is a result of the fact that the gas phase is not diminished as a result of parasitic deposition on the apparatus walls. The gases therefore remain available for [[the]] deposition on the substrate.

5 The deposition illustrated in FIGS. 2-4 of GaN is only given by way of example. As another example of the present invention is the deposition of zinc telluride.

In this case, between the substrate and the Group VI compound diethyltelluride, the Group II compound dimethylzinc is 10 fed into the apparatus.

It is also possible in the deposition of the dielectric (Ba, Sr) titanate, for a mixture of two or three metal organics to be fed between oxygen and the substrate into the apparatus. The metal organics comprise for example a mixture of diketonate of barium and strontium and aloxides of titanium, for example, 15 titanium isopropoxide. Thus between the substrate and the oxygen, of the Group VI compounds, the mixture of these metalorganics is fed into the apparatus.

Furthermore, it is possible to produce respective 20 compounds in layer form each from a suitable combination of metal organics and Group V or Group VI compounds as has been given in Table 1.

FIG. 5 shows a switching device for the gas inlets of an 25 MOCVD apparatus. The collecting line 52 is connected with a supply vessel (not shown) for a carrier gas/metal organics gas mixture and contains the pneumatic 3/2-way valve V2. The collect line 51 is

connected with a supply vessel or carrier gas/Group V or Group VI
gas mixture and contains extends through the pneumatic 3/2-way
valves [3 port/2 position valve] V1. The valves V1 and V2 are
connected via the respective lines with the upper compartment 4'
5 and the lower compartment 5' [[of]] via the respective gas inlets.
In the pressureless state of valve V2 the valve opens into the
upper compartment and the depressurized state of valve V2 the valve
~~opens into the upper compartment and in the depressurized state of~~
10 valve V1, it opens into the lower compartment 5' (see FIG. 5). The
gases are introduced in the state of the art technique into the
apparatus.

Both valves V1 and V2 are connected to a N₂ pressure line
53 over a manually [[-]] operated valve V3 and can be switched over
thereby. In that case, the mixture of the carrier gas or carrier
15 gases and at least one metal organic is then fed under pressure
into the compartment 5' and thus between a substrate on the
susceptor 6 and a mixture of carrier gas or gases and at least one
Group V or Group VI compound. The last-mentioned gas mixture is
then fed into the compartment 4'. The partition plate 1 in FIG. 1
20 has only been shown representationally and extends as shown in
FIGS. 1 and 3 up to the susceptor 6. Thus it is ensured that the
different gas mixtures will never be present simultaneously in one
and the same compartment 4' and 5'. This kind of improvement
enables as reliable and at the same time flexible feed of the gas
25 mixture into the upper and lower compartment 4', 5' of the
apparatus.

Parts list:

3/2-way valves (V1, V2): 1/4 inch VCR-FFF

3/2-way valve (V3) hand-operated, built-in panel valves
(Bosch) 0820 402 024 3/2 WV NG4 (1/8 inch)

5 Stainless steel pipe 8/8 inch electropolished

Pneumatic tubing 1/8 inch

Table 1

Layer Compound	Metal Organic	Group V/Group VI Compound	Carrier Gas
Aluminumgallium arsinide ((AlGa)As)	TMA1 (Trimethylaluminum), TEA1 (Triethylaluminum), TMGa (Trimethylgallium), TEGa (Triethylgallium)	AsH ₃ (Arsine) TBAs (Tert-butylarsine)	H ₂ , N ₂ , Ar
Galliumarsenide (GaAs)	TMGa, TEGa	AsH ₃ , TBAs	H ₂ , N ₂ , Ar
Aluminumarsenide (AlAs)	TMA1, TEA1	AsH ₃ , TBAs	H ₂ , N ₂ , Ar
Galliumindiumarsenide (AlIn)As)	TMGa, TEGa, TMIn	AsH ₃ , TBAs	H ₂ , N ₂ , Ar
Aluminumindiumarsenide ((GaIn)As)	TMA1, TEA1, TMIn	AsH ₃ , TBAs	H ₂ , N ₂ , Ar
Indiumphosphide (InP)	TMIn	PH ₃ , TBP	H ₂ , N ₂ , Ar
Aluminumgalliumindium-phosphide (AlGa _{1-x} In _x P)	TMA1, TEA1, TMGa, TEGa, TMIn (Trimethylindium)	PH ₃ (Phosphino), TBP (Tertiabutylphoshine)	H ₂ , N ₂ , Ar
Galliumindium phosphide ((GaIn)(P))	TMGa, EGa, TMIn	Ph ₃ , TBP	H ₂ , N ₂ , Ar
Aluminumindium phosphide ((AlIn)(P))	TMA1, EA1, TMIn	PH ₃ , TBP	H ₂ , N ₂ , Ar
Galliumindiumarsenidephosphide (((GaIn)(AsP)))	TMGDa, TEGa, TMIn	AsH ₃ , TBAs, PH ₃ , TBP	H ₂ , N ₂ , Ar
Aluminumgalliumindiumarsenide phosphide (AlGaln)(AsP))	TMA1, TEA1, TMGa, TEGa, TMIn	AsH ₃ , TBAs, PH ₃ , TBP	H ₂ , N ₂ , Ar
Aluminumnitride (Aln)	TMA1, TEA1	NH ₃ (Ammonia)	H ₂ , N ₂ , Ar
Gallumnitride (GaN)	TMGa, TEGa	NH ₃	H ₂ , N ₂ , Ar

	Indiumnitride (InN)	TMln	NH ₃	H ₂ , N ₂ , Ar
5	Aluminumgalliumindiumnitride ((AlGaIn)(N))	TMA1, TEA1, TMGa, TEGa, TMln	NH ₃	H ₂ , N ₂ , Ar
	Galliumindiumnitride ((Galn)(N))	TMGa, TEGa, TMln	NH ₃	H ₂ , N ₂ , Ar
	Galliumantimonide (GaSb)	TMGa, TEGa	TMSb (Trimethyl antimony) TESb (Triethyl- antimony)	H ₂ , N ₂ , Ar
10	Aluminumantimonide (AlSb)	TMA1, TEA1	TMSb, TESb	H ₂ , N ₂ , Ar
	Indiumantimonide (InSb)	TMln	TMSb, TESb	H ₂ , N ₂ , Ar
	Aluminumindiumantimonide (AlIn)Sb))	TMA1, EA1, TMln	TMSb, TESb	H ₂ , N ₂ , Ar
	Galliumindiumantimonide ((GaIn)Sb))	TMGa, TEGa, TMln	TMSb, TESb	H ₂ , N ₂ , Ar
15	Galliumarsenideantimonide (Ga(AsSb))	TMGa, TEGa	PH ₃ , TBP, TMSb, TESb	H ₂ , N ₂ , Ar
	Aluminumarsenideantimonide (Al(AsSb))	TMA1, TEA1	AsH ₃ , TBAs, TMSb, TESb	H ₂ , N ₂ , Ar
20	Indiumarsenideantimonide (In(AsSb))	TMln	AsH ₃ , TBAs, TMSb, TESb	H ₂ , N ₂ , Ar
	Galliumindiumarsenide- antimonide(GaIn)(AsSb))	TMGa, EGA, TMln	AsH ₃ , TBAs, TMSb, TESb	H ₂ , N ₂ , Ar
	Galliumphosphideantimonide (GaPSb))	TMGa, TEGa	PH ₃ , TBP, TMSb, TESb	H ₂ , N ₂ , Ar
25	Indiumphosphideantimonide (In(PSb))	TMln	PH ₃ , TBJP, TMSb, TESb	H ₂ , N ₂ , Ar
	Indiumphosphidearsenide- antimonide (In(PAsSb))	TMln	PH ₃ , TBP, AsH ₃ , TBAs, TMSb, TESb	H ₂ , N ₂ , Ar
	Cadmiumtelluride (CdTe)	DMCd (Dimethyl-cadmium)	DETe Diethyltellurium) DMTe Dimethyl- tellurium, DlPe (Diisopropyl- tellurium)	H ₂ , N ₂ , Ar
30	Mercurytelluride (Hg/Te)	Hg (Mercury)	DETe	H ₂ , N ₂ , Ar
	Cadmiummercury telludride ((CdHg)Te)	DMCd, HGD	DETe	H ₂ , N ₂ , Ar

Zincsulfide (ZnS)	DMZn (Dimethyl-zinc), DEZn (Diethylzinc)	H ₂ S Hydrogen-sulfide, DES (Diethylsulfide), DTBS (Ditert-butylsulfide)	H ₂ , N ₂ , Ar
Zincselenide (ZnSe)	DMZn (Dimethylzinc), DEZn (Diethylzinc)	DMSe (Dimethyl-selenide), DESe Diethylselenium, DIPSe(Diisopropyl selenium), DTBSe (Ditert-butylselenium)	H ₂ , N ₂ , Ar
Bariumstrontiumtitanate ((BaSr)TiO ₃)	Ba(thd) ₂ , (Barium/Strontium tetramethylheptanedionat), Ba(hfa) ₂ , (Barium//Strontiumhexafluoroacetylacetone), TIB (Titaniumtetrakisopropoxide), TTB (Titaniumetrakisterbutoxide),	O ₂ (Oxygen), O ₃ (Ozone), N ₂ O (laughing gas)	N ₂ , Ar
leadzirconatetitanate (Pb(ZrTi)O ₃)	TEL (Tetraethyl lead), TEL (Tetraphenyllead Pb(thd) ₂ , (Leadtetramethylheptanedi onate), ZTP (Zirconiumtetrakis(isopropoxide) TIP, TTB	O ₂	